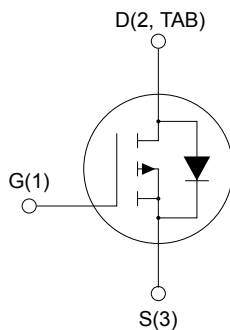


P-channel 30 V, 10 mΩ typ., 52 A, STripFET H6 Power MOSFET in a DPAK package


DPAK


AM11258v1

Features

Order codes	V _{DSS}	R _{DS(on)} max	I _D	P _{TOT}
STD52P3LLH6	30 V	12 mΩ	52 A	70 W

- Very low on-resistance
- Very low gate charge
- High avalanche ruggedness
- Low gate drive power loss

Applications

- Switching applications

Description

This device is a P-channel Power MOSFET developed using the STripFET H6 technology with a new trench gate structure. The resulting Power MOSFET exhibits very low R_{DS(on)} in all packages.



Product status link

[STD52P3LLH6](#)

Product summary

Order code	STD52P3LLH6
Marking	52P3LLH6
Package	DPAK
Packing	Tape and reel

Note: For the P-channel Power MOSFETs the actual polarity of the voltages and the current must be reversed.

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	30	V
V_{GS}	Gate-source voltage	± 20	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	52	A
	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	37.5	A
$I_{DM}^{(1)}$	Drain current (pulsed)	208	A
P_{TOT}	Total power dissipation at $T_C = 25\text{ }^\circ\text{C}$	70	W
T_{stg}	Storage temperature	-55 to 175	$^\circ\text{C}$
T_J	Max. operating junction temperature	175	$^\circ\text{C}$

1. Pulse width limited by safe operating area.

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	2.14	$^\circ\text{C/W}$

Note: For the P-channel Power MOSFETs the actual polarity of the voltages and the current must be reversed.

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 3. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown Voltage	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0\ \text{V}$	30			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\ \text{V}$, $V_{DS} = 30\ \text{V}$			1	μA
		$V_{GS} = 0\ \text{V}$, $V_{DS} = 30\ \text{V}$, $T_C = 125\text{ °C}$			10	μA
I_{GSS}	Gate-body leakage current	$V_{GS} = \pm 20\ \text{V}$, $V_{DS} = 0\ \text{V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	1		2.5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\ \text{V}$, $I_D = 26\ \text{A}$		10	12	m Ω
		$V_{GS} = 4.5\ \text{V}$, $I_D = 26\ \text{A}$		14	17	m Ω

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\ \text{V}$, $f = 1\ \text{MHz}$, $V_{GS} = 0\ \text{V}$	-	3350	-	pF
C_{oss}	Output capacitance		-	414	-	pF
C_{rSS}	Reverse transfer capacitance		-	287	-	pF
Q_g	Total gate charge	$V_{DD} = 15\ \text{V}$, $I_D = 52\ \text{A}$, $V_{GS} = 4.5\ \text{V}$ (see Figure 13. Gate charge test circuit)	-	33	-	nC
Q_{gs}	Gate-source charge		-	14	-	nC
Q_{gd}	Gate-drain charge		-	11	-	nC

Table 5. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 24\ \text{V}$, $I_D = 15\ \text{A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\ \text{V}$ (see Figure 12. Switching times test circuit for resistive load)	-	12.8	-	ns
t_r	Rise time		-	112	-	ns
$t_{d(off)}$	Turn-off delay time		-	61	-	ns
t_f	Fall time		-	45	-	ns

Note: For the P-channel Power MOSFETs the actual polarity of the voltages and the current must be reversed.

Table 6. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{SD}^{(1)}$	Forward on voltage	$I_{SD} = 52\text{ A}$, $V_{GS} = 0\text{ V}$	-		1.1	V
t_{rr}	Reverse recovery time	$I_{SD} = 52\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 24\text{ V}$	-	25.2		ns
Q_{rr}	Reverse recovery charge	(see Figure 14. Test circuit for inductive load switching and diode recovery times)	-	17.4		nC
I_{RRM}	Reverse recovery current		-	1.4		A

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%.

Note: For the P-channel Power MOSFETs the actual polarity of the voltages and the current must be reversed.

2.1 Electrical characteristics (curves)

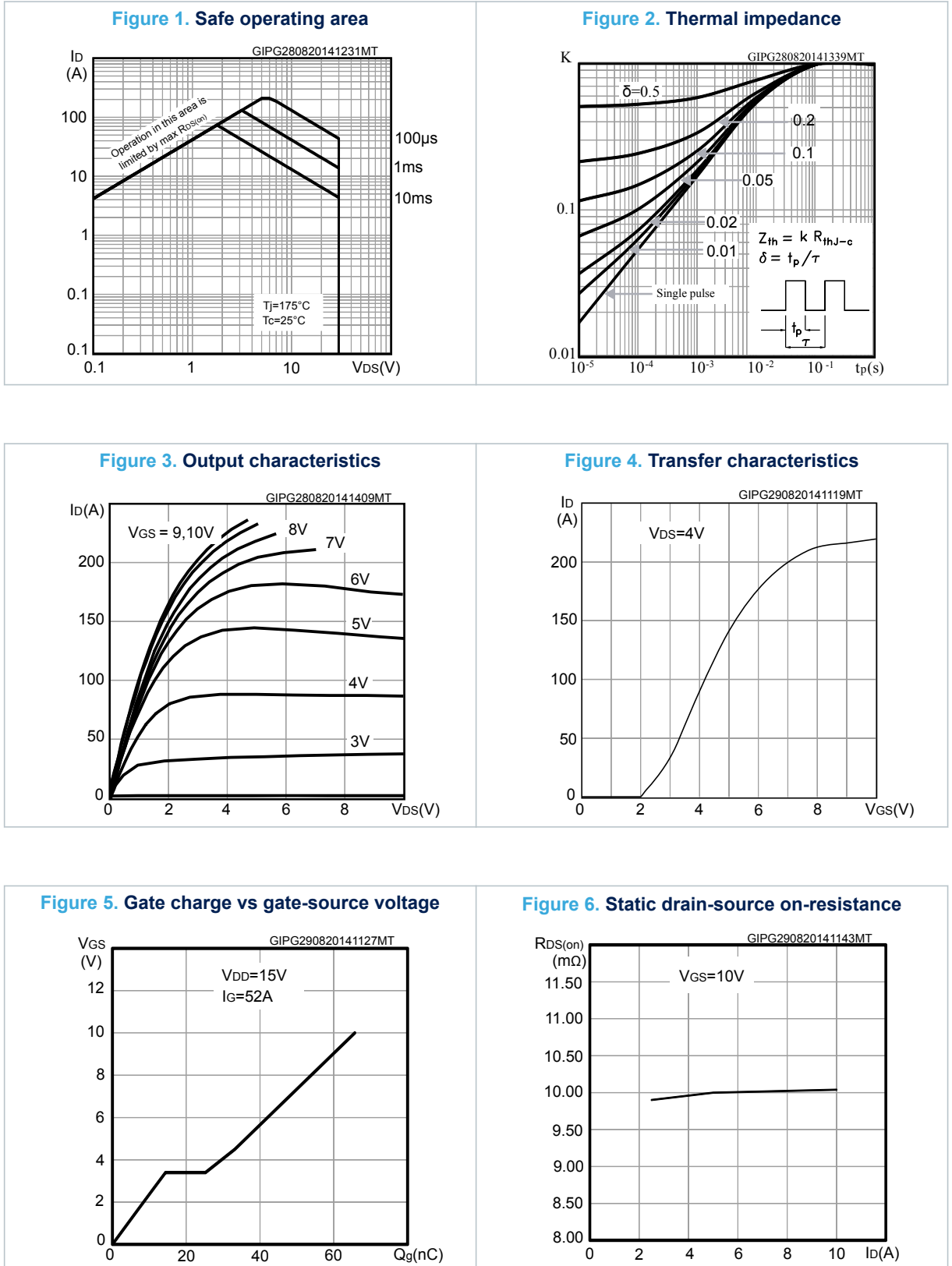


Figure 7. Capacitance variations

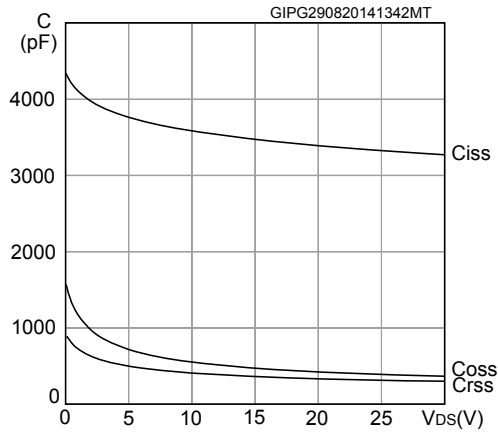


Figure 8. Normalized gate threshold voltage vs temperature

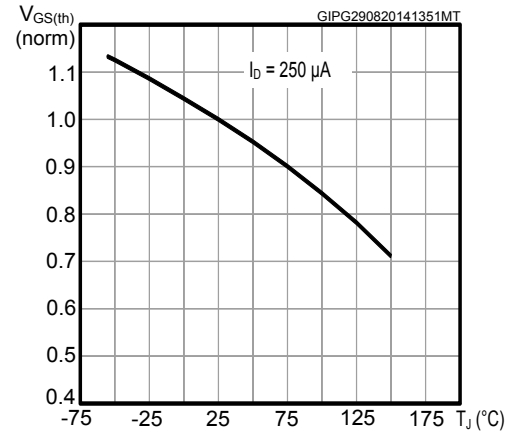


Figure 9. Normalized on-resistance vs temperature

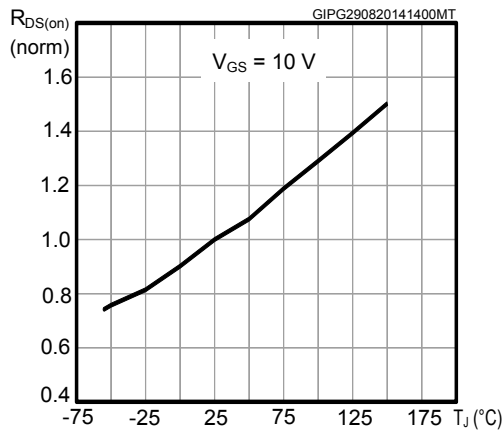


Figure 10. Normalized $V_{(BR)DSS}$ vs temperature

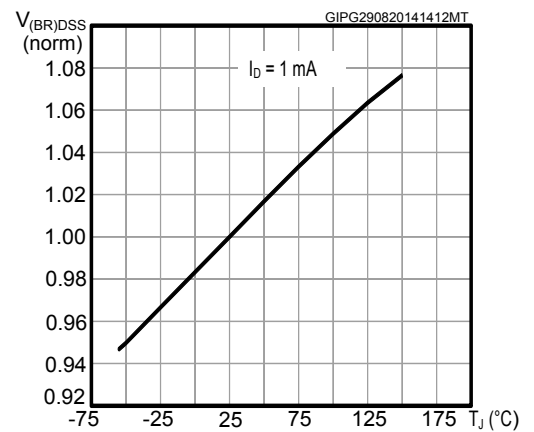
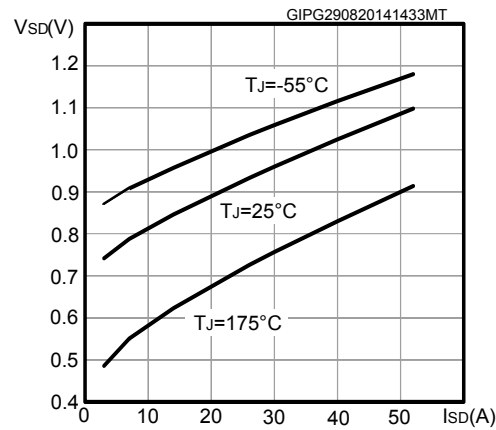
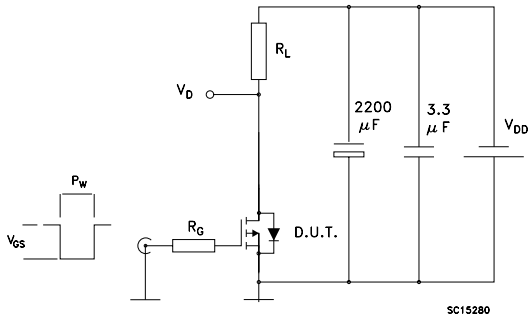
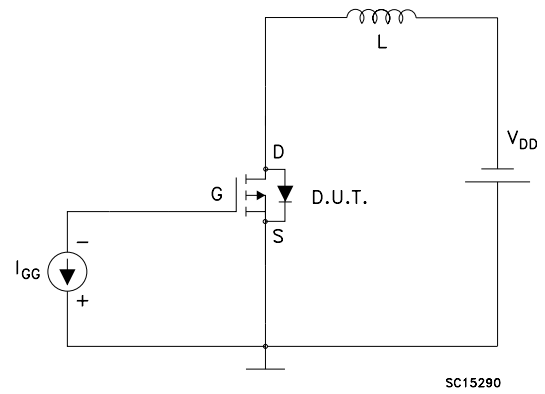
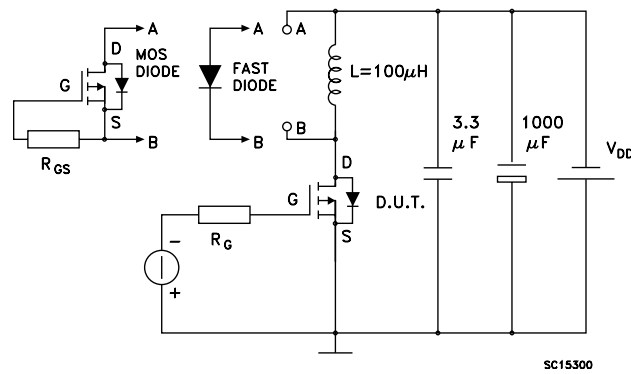


Figure 11. Source-drain diode forward characteristics



3 Test circuits

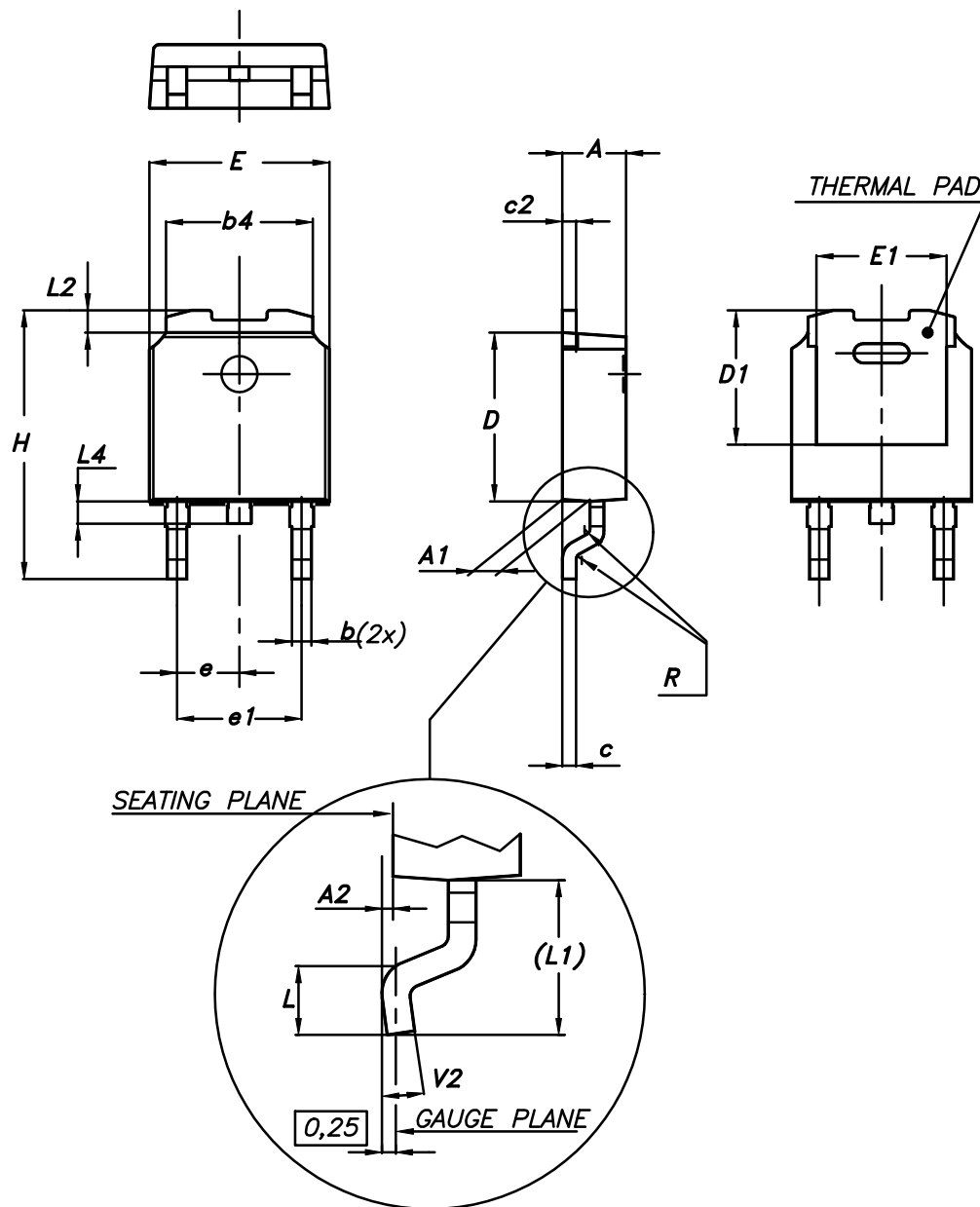
Figure 12. Switching times test circuit for resistive load

Figure 13. Gate charge test circuit

Figure 14. Test circuit for inductive load switching and diode recovery times


4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 DPAK (TO-252) type A package information

Figure 15. DPAK (TO-252) type A package outline

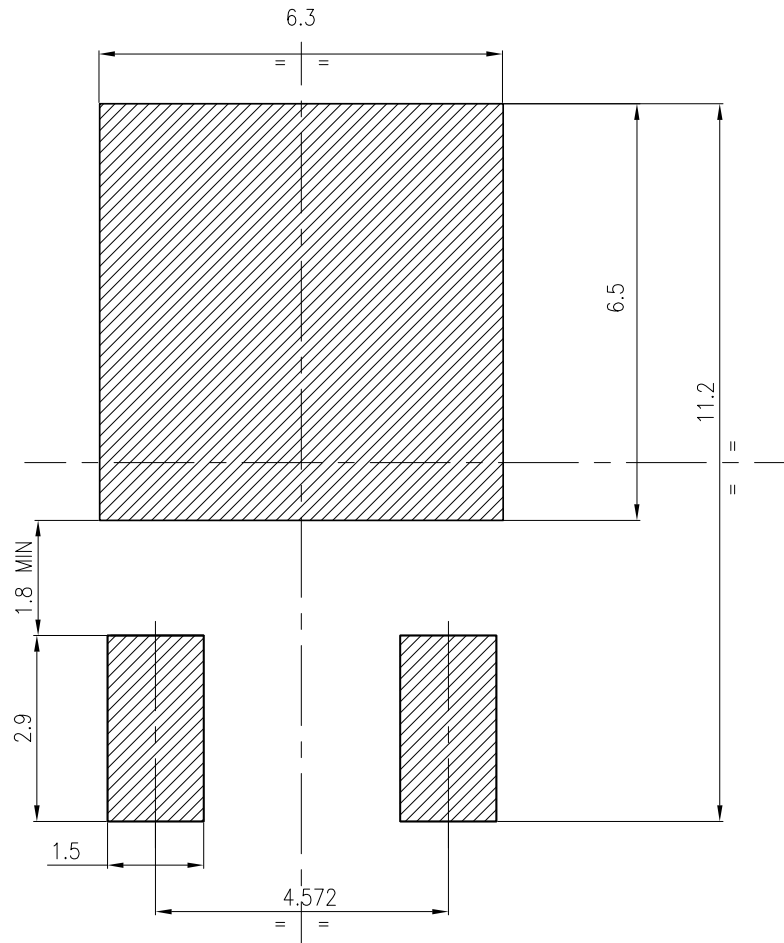


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Table 7. DPAK (TO-252) type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	4.60	4.70	4.80
e	2.159	2.286	2.413
e1	4.445	4.572	4.699
H	9.35		10.10
L	1.00		1.50
(L1)	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

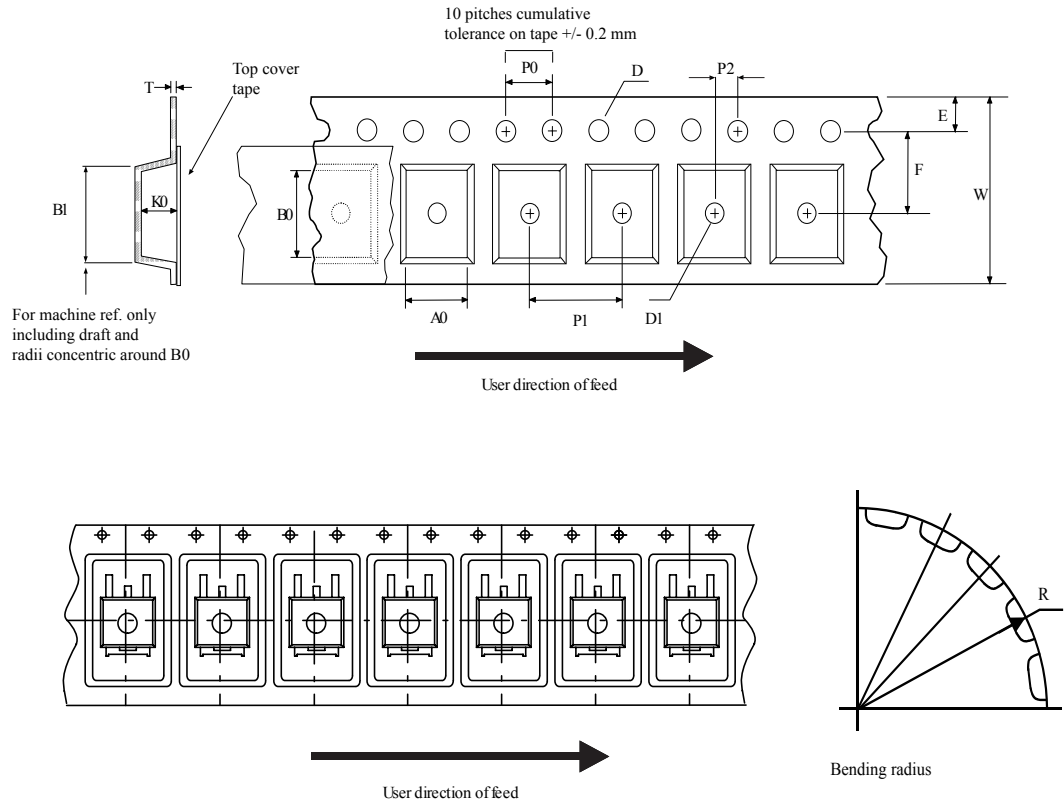
Figure 16. DPAK (TO-252) type A recommended footprint (dimensions are in mm)



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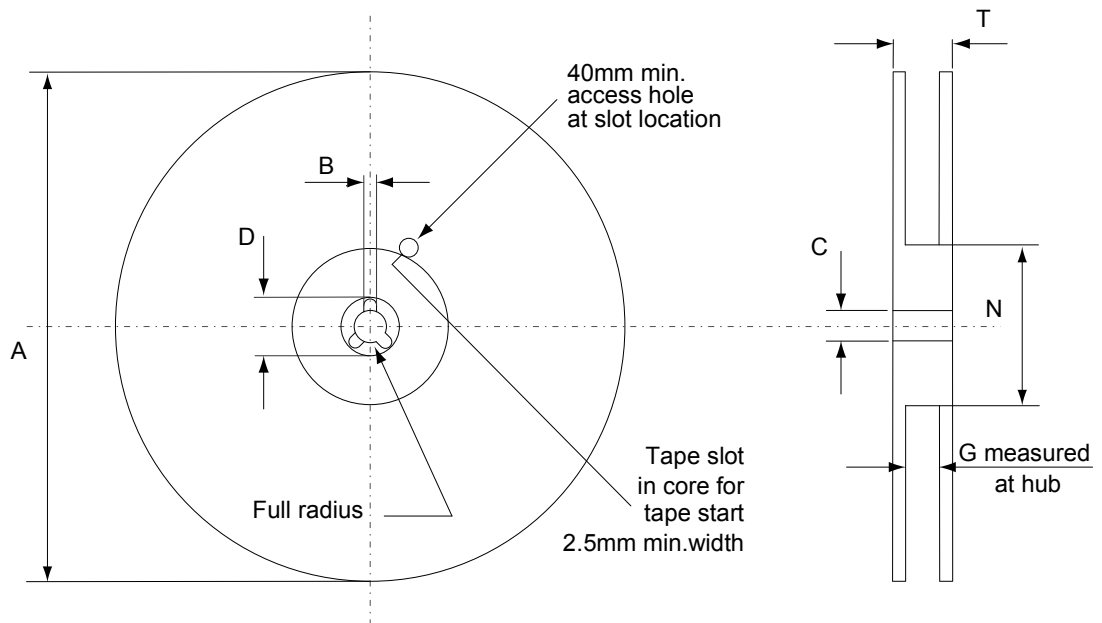
4.2 DPAK (TO-252) packing information

Figure 17. DPAK (TO-252) tape outline



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Figure 18. DPAK (TO-252) reel outline



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Table 8. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Revision history

Table 9. Document revision history

Date	Revision	Changes
02-Jun-2014	1	First release
24-Sep-2014	2	Updated the title, the features and the description in cover page. Updated <i>Table 2: "Absolute maximum ratings"</i> , <i>Section 2: "Electrical characteristics"</i> . Added <i>Section 2.1: "Electrical characteristics (curves)"</i> . Minor text changes.
11-Feb-2020	3	Datasheet status promoted from preliminary to production data. Minor text changes.

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